

ABSTRACT

A polishing composition of the present invention, which is used in precision polishing the surface of a wafer for semiconductor devices, remarkably reduces haze that occurs on the surface of the wafer. The polishing composition includes silicon dioxide, an alkaline compound, a water-soluble polymer, and water. The silicon dioxide is colloidal silica or fumed silica. The average primary particle diameter D_{SA} of the colloidal silica is from 5 to 30 nm, and the average secondary particle diameter D_{N4} of the colloidal silica is from 5 to 120 nm. The average primary particle diameter D_{SA} of the fumed silica is from 5 to 30 nm, and the average secondary particle diameter D_{N4} of the fumed silica is from 5 to 200 nm.